

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2209	(257/774).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 15:56
S2	30	(US-20020041028-\$ or US-20020117737-\$ or US-20030001278-\$ or US-20030020168-\$ or US-20030020169-\$ or US-20030085473-\$ or US-20030155657-\$ or US-20030183939-\$ or US-20030205825-\$ or US-20030218256-\$ or US-20040119164-\$ or US-20040130030-\$ or US-20040130035-\$ or US-20040188850-\$ or US-20050012223-\$ or US-20050093108-\$ or US-20050093168-\$).did. or (US-5739579-\$ or US-5990011-\$ or US-6037664-\$ or US-6083822-\$ or US-6144099-\$ or US-6359328-\$ or US-6559546-\$ or US-6686662-\$ or US-6734116-\$ or US-6794693-\$ or US-6873057-\$ or US-6879042-\$ or US-6885105-\$).did.	US-PGPUB; USPAT	OR	ON	2005/05/09 09:03
S3	996	(438/672).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 09:21
S4	1451	(438/687).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 09:40
S5	889	damascene and "etch stop".ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:41

S6	197	damascene and "etch stop".ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:47
S7	34	damascene and ("etch stop" with (composit or multi-layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 09:50
S8	121	damascene and ("etch stop" with (composite or multi-layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 16:28

S9	72	(US-20020041028-\$ or US-20020117737-\$ or US-20030001278-\$ or US-20030020168-\$ or US-20030020169-\$ or US-20030085473-\$ or US-20030155657-\$ or US-20030183939-\$ or US-20030205825-\$ or US-20030218256-\$ or US-20040119164-\$ or US-20040130030-\$ or US-20040130035-\$ or US-20040188850-\$ or US-20050012223-\$ or US-20050093108-\$ or US-20050093168-\$ or US-20030207562-\$ or US-20030113995-\$ or US-20020039836-\$ or US-20050006776-\$ or US-20040166674-\$ or US-20030042613-\$ or US-20020019131-\$ or US-20010054765-\$ or US-20010004550-\$).did. or (US-20050023694-\$ or US-20040186223-\$ or US-20040147100-\$ or US-20030134521-\$ or US-20030096090-\$ or US-20030089992-\$ or US-20010034121-\$ or US-20040191977-\$ or US-20020140103-\$).did. or (US-5739579-\$ or US-5990011-\$ or US-6037664-\$ or US-6083822-\$ or US-6144099-\$ or US-6359328-\$ or US-6559546-\$ or US-6686662-\$ or US-6734116-\$ or US-6794693-\$ or US-6873057-\$ or US-6879042-\$ or US-6885105-\$ or US-6830971-\$ or US-6777323-\$ or US-6683002-\$ or US-6589863-\$ or US-6495448-\$ or US-6251770-\$ or US-6153514-\$ or US-5904565-\$ or US-6562712-\$ or US-6551872-\$ or US-6440840-\$ or US-6391713-\$ or US-6365506-\$). did. or (US-6331479-\$ or US-5968333-\$ or US-6831366-\$ or US-6734110-\$ or US-6455417-\$ or US-6440838-\$ or US-6753260-\$ or US-6424021-\$ or US-5935762-\$ or US-6107188-\$).did. or (US-6107188-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2005/05/09 09:58
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S10	3	("6177364" "6440838" "6498399").PN. OR ("6734116").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/09 10:32
S11	273	taiwan.as. and damascene and "etch stop"	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/09 10:32
S12	358	taiwan.as. and damascene and "etch stop"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:47
S13	2	("6734116").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 10:40
S14	61	damascene and ("etch stop" with (composite or multi-layer)) and "low-k"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 12:26
S15	2	("6753260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 12:26
S16	130	S12 and "low-k"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:17
S17	182	("spin on glass" or SOG) and "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:17
S18	32	("spin on glass" or SOG) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:23

S19	1	("spin on polymer" or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:24
S20	1	("spin-on-polymer" or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:24
S21	1	((spin adj on adj polymer) or SOp) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:25
S22	32	((spin adj on adj glass) or SOG) with "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:33
S23	8	"film hardness" and FSG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:36
S24	0	hardness with "spin of glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37
S25	0	hardness with "spin on glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37
S26	0	hardness same "spin on glass"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:37

S27	17	hardness with SOG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:49
S28	8	GPa with SOG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:51
S29	0	hardness and spin adj on adj glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:07
S30	17	(etch\$3 near2 selectivity) with (SiCN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:14
S31	2	(etch\$3 near2 selectivity) with (SiCN and SiCO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:19
S32	7	(etch\$3 near2 selectivity) with (SiCN and (SiCO or SiOC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:53
S33	0	("10365924").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:32
S34	0	"10365924".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:33

S35	17	(etch\$3 adj selectivity) with (SiCN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:39
S36	0	("200400161535").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:41
S37	2	("0161535").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 15:40
S38	5	"414467".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:41
S39	114	S12 and selectivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:48
S40	8	(selectivity) with (SiCN and (SiCO or SiOC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:53
S41	50	damascene and ("etch stop" with (composite or multi-layer)) and "silicon carbide" and ("silicon dioxide" or "silicon oxide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 09:15
S42	2	("6753260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 10:57

S43	2	("6873057").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 13:28
S44	0	("s9and(OSGnear2"dielectriclayer")").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 13:29

S48	100	damascene and (dielectric or ILD) near2 ("organo-silicate glass" or osg)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 13:32
S49	265	damascene and "compressive stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:54
S50	118	damascene and "compressive stress" with layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 15:58
S51	81	damascene and "compressive stress" with layer and "tensile stress"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:35
S52	2	damascene and "compressive stress" with "tensile stress" with etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:47
S53	0	("2005/0110153").URPN.	USPAT	OR	ON	2005/11/18 16:46
S54	17	damascene and "compressive stress" same "tensile stress" same etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:02
S55	9	damascene and "compressive stress" with (es or "etch stop")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:07
S56	4	"compressive stress" with (SiCN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:05

S57	1196	(es or "etch stop") with dyne\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:30
S58	45	("etch stop") with dyne\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:31
S59	0	("etch stop") with dyne\$3 with (SiCN or SiCO or SiN or SiO or SiC or SiO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:15

S61	4	damascene with dyne\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:32
S62	32	damascene and dyne\$3 with layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:37
S63	8	"film hardness" and "elastic modulus" and damascene	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 17:37